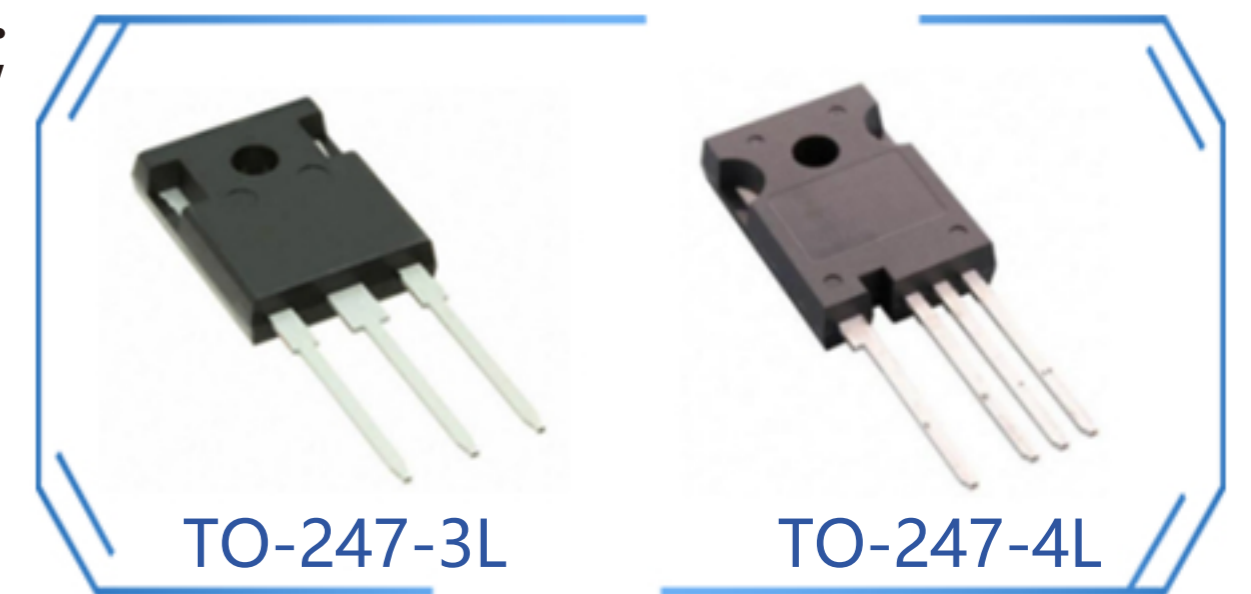


IGBT Micro Trench Discrete for PV/Eenergy Storage/EV Charger Application

Product Introduction

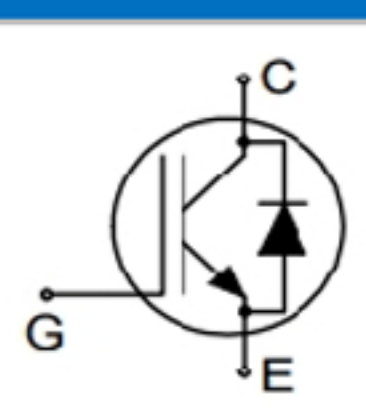
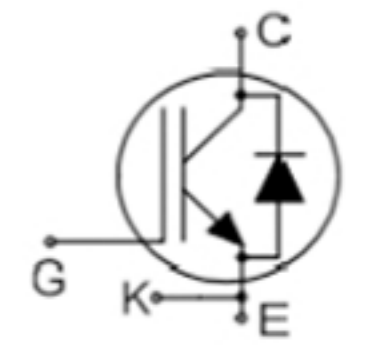
- 1、 TO-247-3L/TO-247-4L and other packages;
- 2、 650V 50A, Si and SiC hybrid packaging products for different applications;
- 3、 It is mainly used for PV/EV charger/Eenergy Storage applications, and adopts advanced trench design technology to meet the requirements of high efficiency of power devices in power conversion system;
- 4、 Other market mainstream products can be completely pin to pin replaced by our related series products;
- 5、 Use environmentally friendly materials and meet RoHS standards;



Product Features

- 1、 1.6um micro-trench design, excellent product performance, with low Vce(sat) and fast switching characteristics;
- 2、 S series product with medium speed for 20-30Khz application demand and H series product with high speed for 30-40Khz;
- 3、 Tjmax=175°C,high reliability;

Electrical Parameters

Part No.	Specification	Vcesat@25°C	Eoff@25°C	Diode	Package	Structure
DGW50N65CTS2A	50A/650V	1.45V	0.55mJ	Si diode	TO-247-3L	
DGW50N65CTH2A	50A/650V	1.70V	0.35mJ			
DGWC50N65CTS2A	50A/650V	1.45V	0.55mJ	Sic diode		
DGWC50N65CTH2A	50A/650V	1.70V	0.35mJ			
DGZ50N65CTS2A	50A/650V	1.45V	0.55mJ	Si diode	TO-247-4L	
DGZ50N65CTH2A	50A/650V	1.70V	0.35mJ			
DGZC50N65CTS2A	50A/650V	1.45V	0.55mJ	Sic diode		
DGZC50N65CTH2A	50A/650V	1.70V	0.35mJ			

Please Refer To The Official Website For More Details

Application



PV



Energy Storage



EV Charger